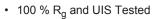
# N-Channel 80 V (D-S) Super Junction Power MOSFET

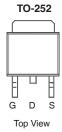
PRODUCT SUMMARY						
V <sub>(BR)DSS</sub> (V)	$r_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A) <sup>c</sup>	Q <sub>g</sub> (Typ.)			
80	0.0029 at V <sub>GS</sub> = 10 V	140	90 nC			
	0.0042 at V <sub>GS</sub> = 4.5 V	90	30110			

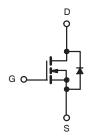
#### **FEATURES**











N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)							
Parameter	Symbol	Limit	Unit				
Gate-Source Voltage	V <sub>GS</sub>	± 20	V				
Continuous Drain Current (T <sub>.I</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	I <sub>D</sub>	140				
Continuous Drain Current (1) = 175 C)	T <sub>C</sub> = 100 °C	טי	90 <sup>a</sup>				
Pulsed Drain Current	I <sub>DM</sub>	560	А				
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	135					
Avalanche Current		I <sub>AS</sub>	140				
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	300	mJ			
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	Pn	425	W			
waxiinani i owei Dissipation	T <sub>C</sub> = 125 °C	, в	150				
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C			

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 sec	R <sub>thJA</sub>	10	15	°C/W		
Maximum Junction-to-Ambient	Steady State		20	35			
Maximum Junction-to-Case		$R_{thJC}$	0.75	1.0			

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t \le 10 \text{ s.}$



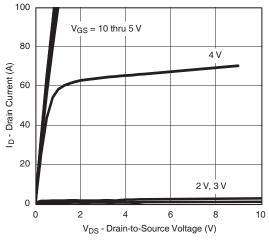


Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
Static				<u>'</u>	<u> </u>	
Drain-Source Breakdown Voltage V <sub>DS</sub>		$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V			1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			10 μA	
		V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			150	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V	140			Α
		$V_{GS} = 10 \text{ V}, I_D = 30 \text{A}$		0.0029	0.0035	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.0034	0.0040	
Drain-Source On-State Resistance <sup>b</sup>	23(0)	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		0.0042	0.0055	Ω
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 64 V, I <sub>D</sub> = 30 A		85		S
Dynamic	•			<u>'</u>		
Input Capacitance	C <sub>iss</sub>			10050		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 64 \text{ V}, f = 1 \text{ MHz}$		3340		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			460		
Total Gate Charge <sup>c</sup>	Qg			98	120	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 64 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{A}$		20		nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			30		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 64 V, $R_L$ = 0.6 $\Omega$		18	25	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		55	80	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			15	22	
Source-Drain Diode Ratings and Cha	racteristics (	T <sub>C</sub> = 25 °C)				
Pulsed Current	I <sub>SM</sub>				560	Α
Diode Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		0.8	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs		125	196	ns

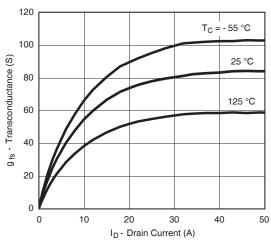
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

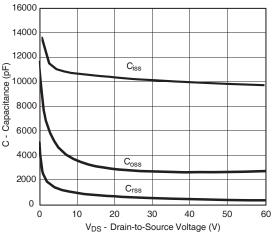
### TYPICAL CHARACTERISTICS (25 °C unless noted)



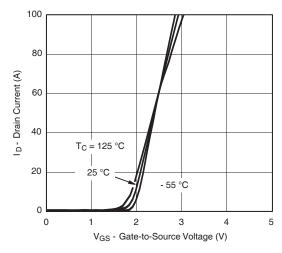
#### **Output Characteristics**



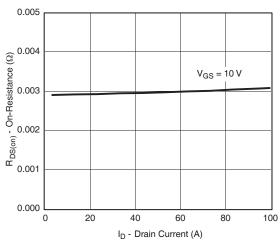
Transconductance



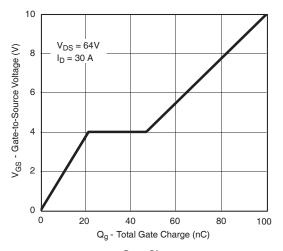
Capacitance



**Transfer Characteristics** 



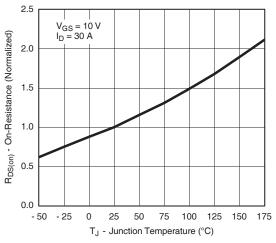
On-Resistance vs. Drain Current



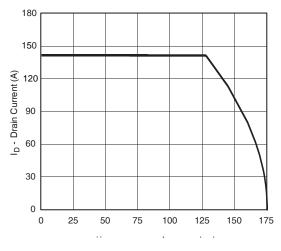
**Gate Charge** 



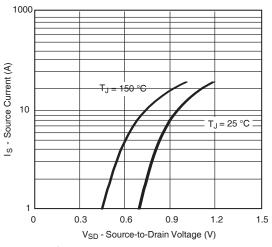
### TYPICAL CHARACTERISTICS (25 °C unless noted)



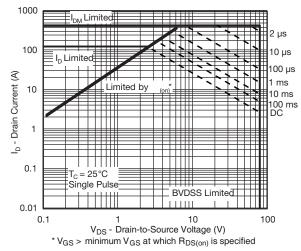
On-Resistance vs. Junction Temperature



Maximum Drain Current vs. Ambient Temperature



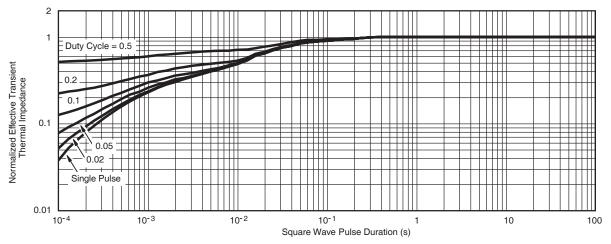
Source-Drain Diode Forward Voltage



Safe Operating Area



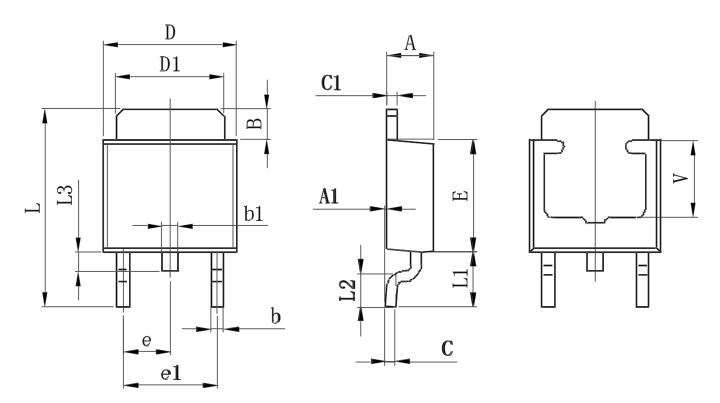
#### THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case



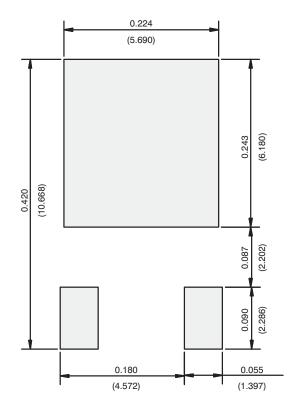
# **TO-252-2L PACKAGE OUTLINE DIMENSIONS**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
В	1.350	1.650	0.053	0.065	
b	0.500	0.700	0.020	0.028	
b1	0.700	0.900	0.028	0.035	
С	0.430	0.580	0.017	0.023	
c1	0.430	0.580	0.017	0.023	
D	6.350	6.650	0.250	0.262	
D1	5.200	5.400	0.205	0.213	
E	5.400	5.700	0.213	0.224	
е	2.300	2.300 TYP.		).091 TYP.	
e1	4.500	4.700	0.177	0.185	
L	9.500	9.900	0.374	0.390	
L1	2.550	2.900	0.100	0.114	
L2	1.400	1.780	0.055	0.070	
L3	0.600	0.900	0.024	0.035	
V	3.800	REF.	0.150 REF.		



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)



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